

SI7852DP-T1-GE3

SI7852DP-T1-GE3 Information





Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



SI7852DP-T1-GE3 Specifications

Manufacturer Part Number	SI7852DP-T1-GE3
Manufacturer	Vishay Siliconix
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	PowerPAK? SO-8
Series	TrenchFET?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	80V
Current - Continuous Drain (Id) @ 25°C	7.6A (Ta)
Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Vgs(th) (Max) @ Id	2V @ 250µA (Min)
Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	-
Vgs (Max)	$\pm 20 V$
FET Feature	-
Power Dissipation (Max)	1.9W (Ta)
Rds On (Max) @ Id, Vgs	16.5 mOhm @ 10A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	PowerPAK? SO-8
Package / Case	PowerPAK? SO-8
	Report errors?

SI7852DP-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

DISCOVER

SI7852DP-T1-GE3 Payment Methods



SI7852DP-T1-GE3 Shipping Methods



If you have any question about SI7852DP-T1-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com